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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	300
Number of Gates	1000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p1000l-fgg484

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Table 3-2 • Chip Global Pin Name

I/O Type	Beginning of I/O Name	Notes
Single-Ended	GFAO/IOuxwByVz GFA1/IOuxwByVz GFA2/IOuxwByVz	Only one of the I/Os can be directly connected to a chip global at a time.
	GFBO/IOuxwByVz GFB1/IOuxwByVz GFB2/IOuxwByVz	Only one of the I/Os can be directly connected to a chip global at a time.
	GFC0/IOuxwByVz GFC1/IOuxwByVz GFC2/IOuxwByVz	Only one of the I/Os can be directly connected to a chip global at a time.
	GCAO/IOuxwByVz GCA1/IOuxwByVz GCA2/IOuxwByVz	Only one of the I/Os can be directly connected to a chip global at a time.
	GCB0/IOuxwByVz GCB1/IOuxwByVz GCB2/IOuxwByVz	Only one of the I/Os can be directly connected to a chip global at a time.
	GCC0/IOuxwByVz GCC1/IOuxwByVz GCC2/IOuxwByVz	Only one of the I/Os can be directly connected to a chip global at a time.
Differential I/O Pairs	GFAO/IOuxwByVz GFA1/IOuxwByVz	The output of the different pair will drive the chip global.
	GFBO/IOuxwByVz GFB1/IOuxwByVz	The output of the different pair will drive the chip global.
	GFCO/IOuxwByVz GFC1/IOuxwByVz	The output of the different pair will drive the chip global.
	GCAO/IOuxwByVz GCA1/IOuxwByVz	The output of the different pair will drive the chip global.
	GCB0/IOuxwByVz GCB1/IOuxwByVz	The output of the different pair will drive the chip global.
	GCCO/IOuxwByVz GCC1/IOuxwByVz	The output of the different pair will drive the chip global.

Note: Only one of the I/Os can be directly connected to a quadrant at a time.

Global Macro and Placement Selections

Low power flash devices provide the flexibility of choosing one of the three global input pad locations available to connect to a global / quadrant global network. For 60K gate devices and above, if the single-ended I/O standard is chosen, there is flexibility to choose one of the global input pads (the first, second, and fourth input). Once chosen, the other I/O locations are used as regular I/Os. If the differential I/O standard is chosen, the first and second inputs are considered as paired, and the third input is paired with a regular I/O. The user then has the choice of selecting one of the two sets to be used as the global input source. There is also the option to allow an internal clock signal to feed the global network. A multiplexer tree selects the appropriate global input for routing to the desired location. Note that the global I/O pads do not need to feed the global network; they can also be used as regular I/O pads.

Hardwired I/O Clock Source

Hardwired I/O refers to global input pins that are hardwired to the multiplexer tree, which directly accesses the global network. These global input pins have designated pin locations and are indicated with the I/O naming convention Gmn (m refers to any one of the positions where the global buffers is available, and n refers to any one of the three global input MUXes and the pin number of the associated global location, m). Choosing this option provides the benefit of directly connecting to the global buffers, which provides less delay. See Figure 3-11 for an example illustration of the connections, shown in red. If a CLKBUF macro is initiated, the clock input can be placed at one of nine dedicated global input pin locations: GmA0, GmA1, GmA2, GmB0, GmB1, GmB2, GmC0, GmC1, or GmC2. Note that the placement of the global will determine whether you are using chip global or quadrant global. For example, if the CLKBIF is placed in one of the GF pin locations, it will use the chip global network; if the CLKBIF is placed in one of the GA pin locations, it will use quadrant global network. This is shown in Figure 3-12 on page 65 and Figure 3-13 on page 65.

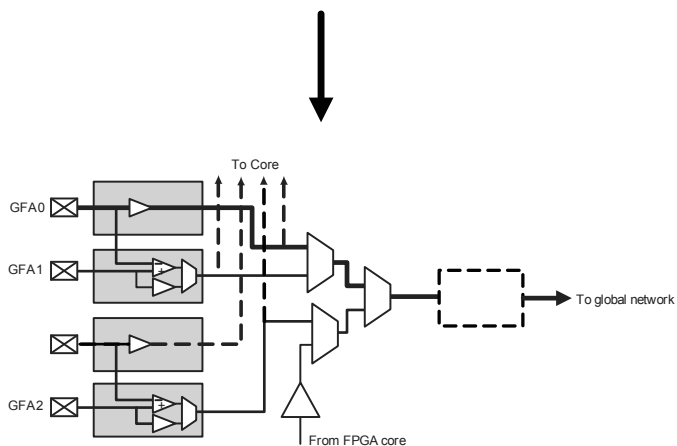


Figure 3-11 • CLKBUF Macro

Each CCC can implement up to three independent global buffers (with or without programmable delay) or a PLL function (programmable frequency division/multiplication, phase shift, and delays) with up to three global outputs. Unused global outputs of a PLL can be used to implement independent global buffers, up to a maximum of three global outputs for a given CCC.

CCC Programming

The CCC block is fully configurable, either via flash configuration bits set in the programming bitstream or through an asynchronous interface. This asynchronous dedicated shift register interface is dynamically accessible from inside the low power flash devices to permit parameter changes, such as PLL divide ratios and delays, during device operation.

To increase the versatility and flexibility of the clock conditioning system, the CCC configuration is determined either by the user during the design process, with configuration data being stored in flash memory as part of the device programming procedure, or by writing data into a dedicated shift register during normal device operation.

This latter mode allows the user to dynamically reconfigure the CCC without the need for core programming. The shift register is accessed through a simple serial interface. Refer to the "UJTAG Applications in Microsemi's Low Power Flash Devices" section on page 363 or the application note *Using Global Resources in Actel Fusion Devices*.

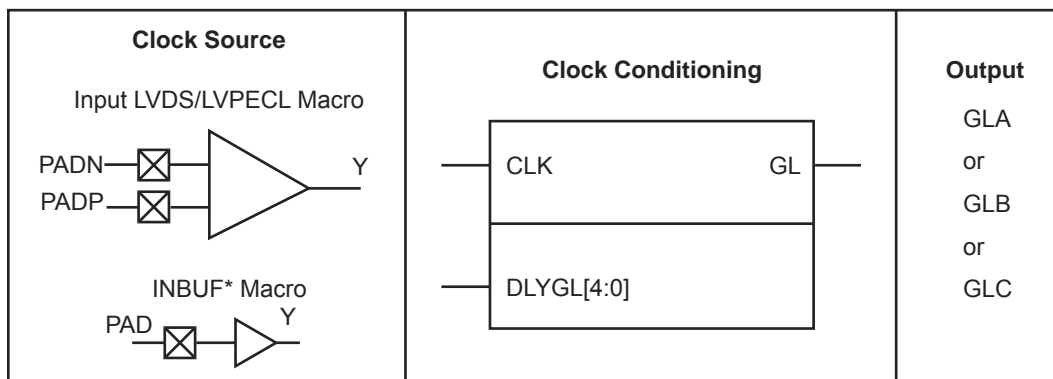
Global Resources

Low power flash and mixed signal devices provide three global routing networks (GLA, GLB, and GLC) for each of the CCC locations. There are potentially many I/O locations; each global I/O location can be chosen from only one of three possibilities. This is controlled by the multiplexer tree circuitry in each global network. Once the I/O location is selected, the user has the option to utilize the CCCs before the signals are connected to the global networks. The CCC in each location (up to six) has the same structure, so generating the CCC macros is always done with an identical software GUI. The CCCs in the corner locations drive the quadrant global networks, and the CCCs in the middle of the east and west chip sides drive the chip global networks. The quadrant global networks span only a quarter of the device, while the chip global networks span the entire device. For more details on global resources offered in low power flash devices, refer to the "Global Resources in Low Power Flash Devices" section on page 47.

A global buffer can be placed in any of the three global locations (CLKA-GLA, CLKB-GLB, or CLKC-GLC) of a given CCC. A PLL macro uses the CLKA CCC input to drive its reference clock. It uses the GLA and, optionally, the GLB and GLC global outputs to drive the global networks. A PLL macro can also drive the YB and YC regular core outputs. The GLB (or GLC) global output cannot be reused if the YB (or YC) output is used. Refer to the "PLL Macro Signal Descriptions" section on page 84 for more information.

Each global buffer, as well as the PLL reference clock, can be driven from one of the following:

- 3 dedicated single-ended I/Os using a hardwired connection
- 2 dedicated differential I/Os using a hardwired connection (not supported for IGLOO nano or ProASIC3 nano devices)
- The FPGA core



Notes:

1. For INBUF* driving a PLL macro or CLKDLY macro, the I/O will be hard-routed to the CCC; i.e., will be placed by software to a dedicated Global I/O.
2. IGLOO nano and ProASIC3 nano devices do not support differential inputs.

Figure 4-3 • CCC Options: Global Buffers with Programmable Delay

The CLKDLY macro is a pass-through clock source that does not use the PLL, but provides the ability to delay the clock input using a programmable delay. The CLKDLY macro takes the selected clock input and adds a user-defined delay element. This macro generates an output clock phase shift from the input clock.

The CLKDLY macro can be driven by an INBUF* macro to create a composite macro, where the I/O macro drives the global buffer (with programmable delay) using a hardwired connection. In this case, the software will automatically place the dedicated global I/O in the appropriate locations. Many specific INBUF macros support the wide variety of single-ended and differential I/O standards supported by the low power flash family. The available INBUF macros are described in the *IGLOO*, *ProASIC3*, *SmartFusion*, and *Fusion Macro Library Guide*.

The CLKDLY macro can be driven directly from the FPGA core. The CLKDLY macro can also be driven from an I/O that is routed through the FPGA regular routing fabric. In this case, users must instantiate a special macro, PLLINT, to differentiate the clock input driven by the hardwired I/O connection.

The visual CLKDLY configuration in the SmartGen area of the Microsemi Libero System-on-Chip (SoC) and Designer tools allows the user to select the desired amount of delay and configures the delay elements appropriately. SmartGen also allows the user to select the input clock source. SmartGen will automatically instantiate the special macro, PLLINT, when needed.

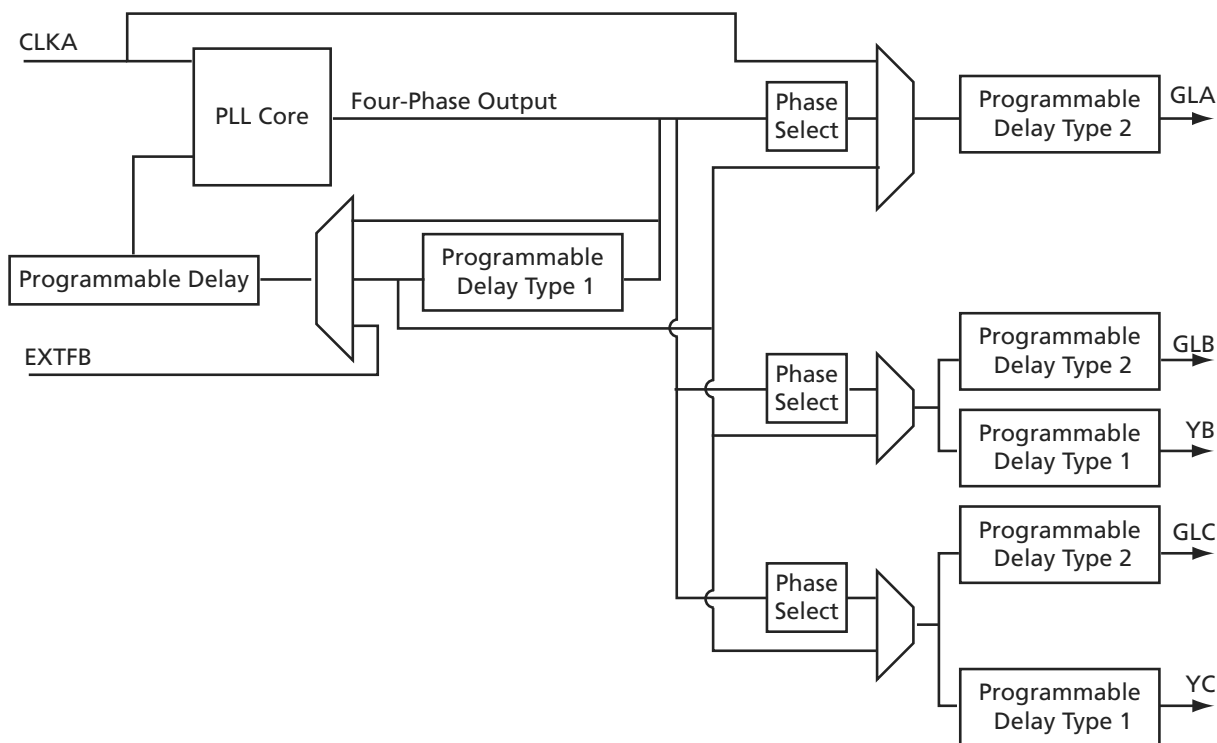
CLKDLY Macro Signal Descriptions

The CLKDLY macro supports one input and one output. Each signal is described in Table 4-2.

Table 4-2 • Input and Output Description of the CLKDLY Macro

Signal	Name	I/O	Description
CLK	Reference Clock	Input	Reference clock input
GL	Global Output	Output	Primary output clock to respective global/quadrant clock networks

SmartGen also allows the user to select the various delays and phase shift values necessary to adjust the phases between the reference clock (CLKA) and the derived clocks (GLA, GLB, GLC, YB, and YC). SmartGen allows the user to select the input clock source. SmartGen automatically instantiates the special macro, PLLINT, when needed.



Note: Clock divider and clock multiplier blocks are not shown in this figure or in SmartGen. They are automatically configured based on the user's required frequencies.

Figure 4-6 • CCC with PLL Block

Global Input Selections

Low power flash devices provide the flexibility of choosing one of the three global input pad locations available to connect to a CCC functional block or to a global / quadrant global network. Figure 4-7 on page 88 and Figure 4-8 on page 88 show the detailed architecture of each global input structure for 30 k gate devices and below, as well as 60 k gate devices and above, respectively. For 60 k gate devices and above (Figure 4-7 on page 88), if the single-ended I/O standard is chosen, there is flexibility to choose one of the global input pads (the first, second, and fourth input). Once chosen, the other I/O locations are used as regular I/Os. If the differential I/O standard is chosen (not applicable for IGLOO nano and ProASIC3 nano devices), the first and second inputs are considered as paired, and the third input is paired with a regular I/O.

The user then has the choice of selecting one of the two sets to be used as the clock input source to the CCC functional block. There is also the option to allow an internal clock signal to feed the global network or the CCC functional block. A multiplexer tree selects the appropriate global input for routing to the desired location. Note that the global I/O pads do not need to feed the global network; they can also be used as regular I/O pads.

IGLOOe and ProASIC3E CCC Locations

IGLOOe and ProASIC3E devices have six CCCs—one in each of the four corners and one each in the middle of the east and west sides of the device (Figure 4-15).

All six CCCs are integrated with PLLs, except in PQFP-208 package devices. PQFP-208 package devices also have six CCCs, of which two include PLLs and four are simplified CCCs. The CCCs with PLLs are implemented in the middle of the east and west sides of the device (middle right and middle left). The simplified CCCs without PLLs are located in the four corners of the device (Figure 4-16).

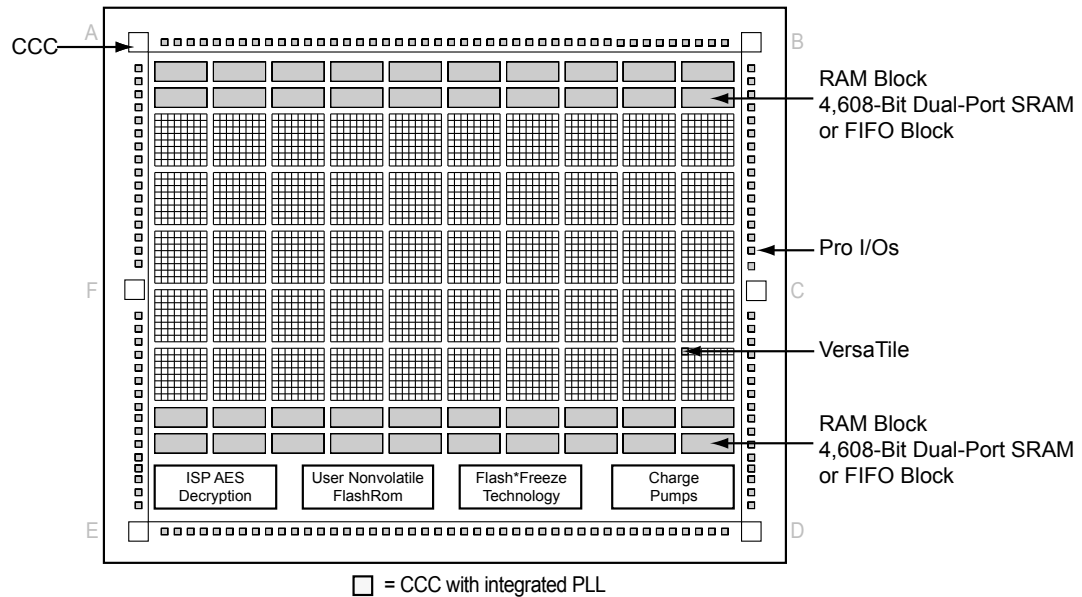


Figure 4-15 • CCC Locations in IGLOOe and ProASIC3E Family Devices (except PQFP-208 package)

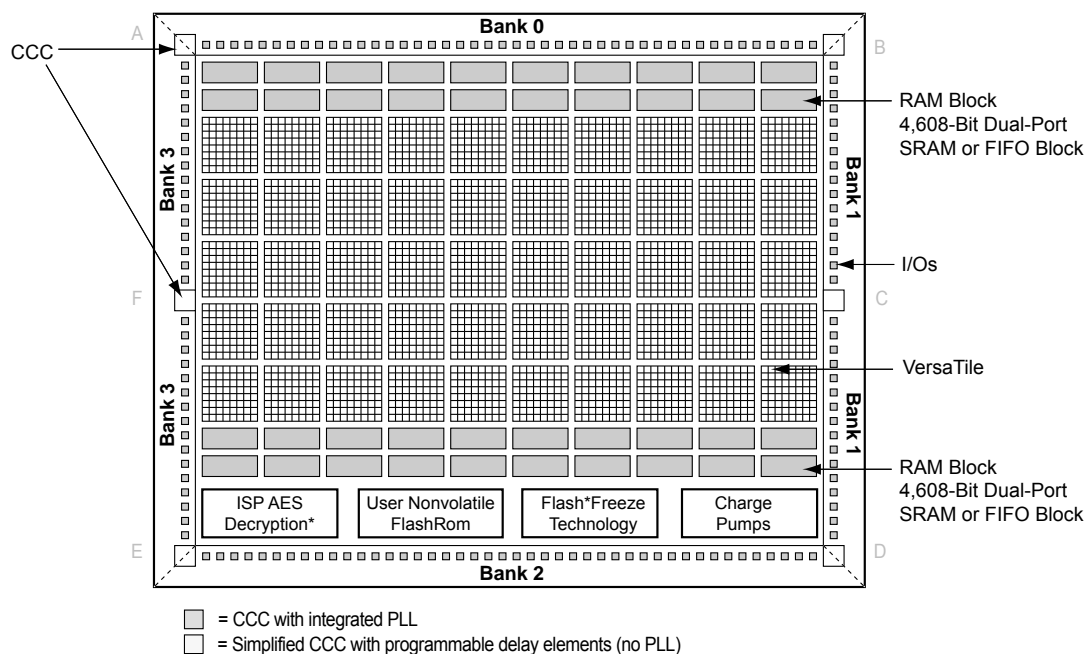


Figure 4-16 • CCC Locations in ProASIC3E Family Devices (PQFP-208 package)

Conclusion

Fusion, IGLOO, and ProASIC3 devices provide users with extremely flexible SRAM blocks for most design needs, with the ability to choose between an easy-to-use dual-port memory or a wide-word two-port memory. Used with the built-in FIFO controllers, these memory blocks also serve as highly efficient FIFOs that do not consume user gates when implemented. The SmartGen core generator provides a fast and easy way to configure these memory elements for use in designs.

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
August 2012	The note connected with Figure 6-3 • Supported Basic RAM Macros, regarding RAM4K9, was revised to explain that it applies only to part numbers of certain revisions and earlier (SAR 29574).	152
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.5 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 6-1 • Flash-Based FPGAs.	150
	IGLOO nano and ProASIC3 nano devices were added to Figure 6-8 • Interfacing TAP Ports and SRAM Blocks.	164
v1.4 (October 2008)	The "SRAM/FIFO Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	150
	The "SRAM and FIFO Architecture" section was modified to remove "IGLOO and ProASIC3E" from the description of what the memory block includes, as this statement applies to all memory blocks.	151
	Wording in the "Clocking" section was revised to change "IGLOO and ProASIC3 devices support inversion" to "Low power flash devices support inversion." The reference to IGLOO and ProASIC3 development tools in the last paragraph of the section was changed to refer to development tools in general.	157
	The "ESTOP and FSTOP Usage" section was updated to refer to FIFO counters in devices in general rather than only IGLOO and ProASIC3E devices.	160
v1.3 (August 2008)	The note was removed from Figure 6-7 • RAM Block with Embedded FIFO Controller and placed in the WCLK and RCLK description.	158
	The "WCLK and RCLK" description was revised.	159
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 6-1 • Flash-Based FPGAs: <ul style="list-style-type: none"> ProASIC3L was updated to include 1.5 V. The number of PLLs for ProASIC3E was changed from five to six. 	150
v1.1 (March 2008)	The "Introduction" section was updated to include the IGLOO PLUS family.	147
	The "Device Architecture" section was updated to state that 15 k gate devices do not support SRAM and FIFO.	147
	The first note in Figure 6-1 • IGLOO and ProASIC3 Device Architecture Overview was updated to include mention of 15 k gate devices, and IGLOO PLUS was added to the second note.	149

I/O Banks

Advanced I/Os are divided into multiple technology banks. Each device has two to four banks, and the number of banks is device-dependent as described above. The bank types have different characteristics, such as drive strength, the I/O standards supported, and timing and power differences.

There are three types of banks: Advanced I/O banks, Standard Plus I/O banks, and Standard I/O banks.

Advanced I/O banks offer single-ended and differential capabilities. These banks are available on the east and west sides of 250K, 400K, 600K, and 1M gate devices.

Standard Plus I/O banks offer LVTTTL/LVCMOS and PCI single-ended I/O standards. These banks are available on the north and south sides of 250K, 400K, 600K, and 1M gate devices as well as all sides of 125K and 60K devices.

Standard I/O banks offer LVTTTL/LVCMOS single-ended I/O standards. These banks are available on all sides of 30K gate devices.

Table 7-4 shows the I/O bank types, devices and bank locations supported, drive strength, slew rate control, and supported standards.

All inputs and disabled outputs are voltage-tolerant up to 3.3 V.

For more information about I/O and global assignments to I/O banks in a device, refer to the specific pin table for the device in the packaging section of the datasheet and the "User I/O Naming Convention" section on page 206.

Table 7-4 • IGLOO and ProASIC3 Bank Type Definitions and Differences

I/O Bank Type	Device and Bank Location	Drive Strength	I/O Standards Supported		
			LVTTTL/ LVCMOS	PCI/PCI-X	LVPECL, LVDS, B-LVDS, M-LVDS
Standard	30 k gate devices (all banks)	Refer to Table 7-14 on page 203	✓	Not Supported	Not Supported
Standard Plus	60 k and 125 k gate devices (all banks)	Refer to Table 7-15 on page 203	✓	✓	Not Supported
	North and south banks of 250 k and 1 M gate devices	Refer to Table 7-15 on page 203	✓	✓	Not Supported
Advanced	East and west banks of 250 k and 1 M gate devices	Refer to Table 7-16 on page 203	✓	✓	✓

I/O Standards

Single-Ended Standards

These I/O standards use a push-pull CMOS output stage with a voltage referenced to system ground to designate logical states. The input buffer configuration, output drive, and I/O supply voltage (V_{CCI}) vary among the I/O standards (Figure 8-6).

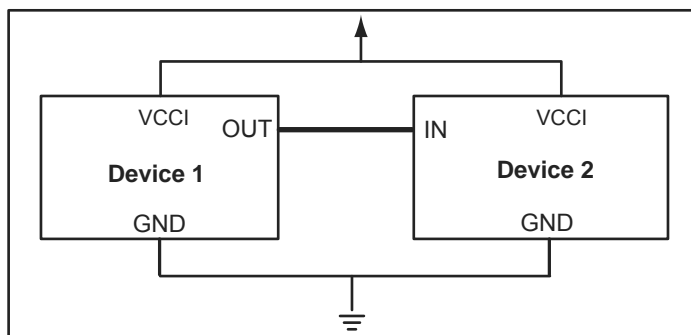


Figure 8-6 • Single-Ended I/O Standard Topology

The advantage of these standards is that a common ground can be used for multiple I/Os. This simplifies board layout and reduces system cost. Their low-edge-rate (dv/dt) data transmission causes less electromagnetic interference (EMI) on the board. However, they are not suitable for high-frequency (>200 MHz) switching due to noise impact and higher power consumption.

LVTTL (Low-Voltage TTL)

This is a general-purpose standard (EIA/JESD8-B) for 3.3 V applications. It uses an LVTTL input buffer and a push-pull output buffer. The LVTTL output buffer can have up to six different programmable drive strengths. The default drive strength is 12 mA. V_{CCI} is 3.3 V. Refer to "I/O Programmable Features" on page 227 for details.

LVC MOS (Low-Voltage CMOS)

The low power flash devices provide four different kinds of LVC MOS: LVC MOS 3.3 V, LVC MOS 2.5 V, LVC MOS 1.8 V, and LVC MOS 1.5 V. LVC MOS 3.3 V is an extension of the LVC MOS standard (JESD8-B-compliant) used for general-purpose 3.3 V applications. LVC MOS 2.5 V is an extension of the LVC MOS standard (JESD8-5-compliant) used for general-purpose 2.5 V applications. LVC MOS 2.5 V for the 30 k gate devices has a clamp diode to V_{CCI} , but for all other devices there is no clamp diode.

There is yet another standard supported by IGLOO and ProASIC3 devices (except A3P030): LVC MOS 2.5/5.0 V. This standard is similar to LVC MOS 2.5 V, with the exception that it can support up to 3.3 V on the input side (2.5 V output drive).

LVC MOS 1.8 V is an extension of the LVC MOS standard (JESD8-7-compliant) used for general-purpose 1.8 V applications. LVC MOS 1.5 V is an extension of the LVC MOS standard (JESD8-11-compliant) used for general-purpose 1.5 V applications.

The V_{CCI} values for these standards are 3.3 V, 2.5 V, 1.8 V, and 1.5 V, respectively. Like LVTTL, the output buffer has up to seven different programmable drive strengths (2, 4, 6, 8, 12, 16, and 24 mA). Refer to "I/O Programmable Features" on page 227 for details.

3.3 V PCI (Peripheral Component Interface)

This standard specifies support for both 33 MHz and 66 MHz PCI bus applications. It uses an LVTTL input buffer and a push-pull output buffer. With the aid of an external resistor, this I/O standard can be 5 V-compliant for low power flash devices. It does not have programmable drive strength.

3.3 V PCI-X (Peripheral Component Interface Extended)

An enhanced version of the PCI specification, 3.3 V PCI-X can support higher average bandwidths; it increases the speed that data can move within a computer from 66 MHz to 133 MHz. It is backward-

compatible, which means devices can operate at conventional PCI frequencies (33 MHz and 66 MHz). PCI-X is more fault-tolerant than PCI. It also does not have programmable drive strength.

Voltage-Referenced Standards

I/Os using these standards are referenced to an external reference voltage (VREF) and are supported on E devices only.

HSTL Class I and II (High-Speed Transceiver Logic)

These are general-purpose, high-speed 1.5 V bus standards (EIA/JESD 8-6) for signaling between integrated circuits. The signaling range is 0 V to 1.5 V, and signals can be either single-ended or differential. HSTL requires a differential amplifier input buffer and a push-pull output buffer. The reference voltage (VREF) is 0.75 V. These standards are used in the memory bus interface with data switching capability of up to 400 MHz. The other advantages of these standards are low power and fewer EMI concerns.

HSTL has four classes, of which low power flash devices support Class I and II. These classes are defined by standard EIA/JESD 8-6 from the Electronic Industries Alliance (EIA):

- Class I – Unterminated or symmetrically parallel-terminated
- Class II – Series-terminated
- Class III – Asymmetrically parallel-terminated
- Class IV – Asymmetrically double-parallel-terminated

SSTL2 Class I and II (Stub Series Terminated Logic 2.5 V)

These are general-purpose 2.5 V memory bus standards (JESD 8-9) for driving transmission lines, designed specifically for driving the DDR SDRAM modules used in computer memory. SSTL2 requires a differential amplifier input buffer and a push-pull output buffer. The reference voltage (VREF) is 1.25 V.

SSTL3 Class I and II (Stub Series Terminated Logic 3.3 V)

These are general-purpose 3.3 V memory bus standards (JESD 8-8) for driving transmission lines. SSTL3 requires a differential amplifier input buffer and a push-pull output buffer. The reference voltage (VREF) is 1.5 V.

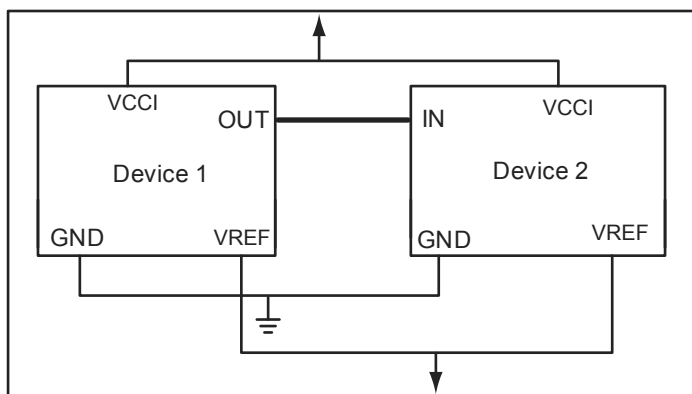


Figure 8-7 • SSTL and HSTL Topology

Power-Up Behavior

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details.

Drive Strength

Low power flash devices have up to seven programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF_S_12 (slew = low, out_drive = 12 mA).

The maximum available drive strength is 24 mA per I/O. Though no I/O should be forced to source or sink more than 24 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected (refer to the "5 V Input and Output Tolerance" section on page 232). Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.

Table 8-19 shows some high-level interfacing examples using low power flash devices.

Table 8-19 • High-Level Interface Examples

Interface	Clock		I/O			
	Type	Frequency	Type	Signals In	Signals Out	Data I/O
GM	Src Sync	125 MHz	LVTTL	8	8	125 Mbps
TBI	Src Sync	125 MHz	LVTTL	10	10	125 Mbps
XSBI	Src Sync	644 MHz	LVDS	16	16	644 Mbps
XGMI	Src Sync DDR	156 MHz	HSTL1	32	32	312 Mbps
FlexBus 3	Sys Sync	104 MHz	LVTTL	≤ 32	≤ 32	≤ 104
Pos-PHY3/SPI-3	Sys Sync	104	LVTTL	8,16,32	8,16,32	≤ 104 Mbps
FlexBus 4/SPI-4.1	Src Sync	200 MHz	HSTL1	16,64	16,64	200 Mbps
Pos-PHY4/SPI-4.2	Src Sync DDR	≥ 311 MHz	LVDS	16	16	≥ 622 Mbps
SFI-4.1	Src Sync	622 MHz	LVDS	16	16	622 Mbps
CSIX L1	Sys Sync	≤ 250 MHz	HSTL1	32,64,96,128	32,64,96,128	≤ 250 Mbps
Hyper Transport	Sys Sync DDR	≤ 800 MHz	LVDS	2,4,8,16	2,4,8,16	≤ 1.6 Gbps
Rapid I/O Parallel	Sys Sync DDR	250 MHz – 1 GHz	LVDS	8,16	8,16	≤ 2 Gbps
Star Fabric	CDR		LVDS	4	4	622 Mbps

Note: Sys Sync = System Synchronous Clocking, Src Sync = Source Synchronous Clocking, and CDR = Clock and Data Recovery.

Output Buffers

There are two variations: Regular and Special.

If the **Regular** variation is selected, only the Width (1 to 128) needs to be entered. The default value for Width is 1.

The **Special** variation has Width, Technology, Output Drive, and Slew Rate options.

Bidirectional Buffers

There are two variations: Regular and Special.

The **Regular** variation has Enable Polarity (Active High, Active Low) in addition to the Width option.

The **Special** variation has Width, Technology, Output Drive, Slew Rate, and Resistor Pull-Up/-Down options.

Tristate Buffers

Same as Bidirectional Buffers.

DDR

There are eight variations: DDR with Regular Input Buffers, Special Input Buffers, Regular Output Buffers, Special Output Buffers, Regular Tristate Buffers, Special Tristate Buffers, Regular Bidirectional Buffers, and Special Bidirectional Buffers.

These variations resemble the options of the previous I/O macro. For example, the Special Input Buffers variation has Width, Technology, Voltage Level, and Resistor Pull-Up/-Down options. DDR is not available on IGLOO PLUS devices.

4. Once the desired configuration is selected, click the **Generate** button. The Generate Core window opens (Figure 9-4).
 5. Enter a name for the macro. Click **OK**. The core will be generated and saved to the appropriate location within the project files (Figure 9-5 on page 257).
-

Figure 9-4 • Generate Core Window

6. Instantiate the I/O macro in the top-level code.

The user must instantiate the DDR_REG or DDR_OUT macro in the design. Use SmartGen to generate both these macros and then instantiate them in your top level. To combine the DDR macros with the I/O, the following rules must be met:

Signal Integrity While Using ISP

For ISP of flash devices, customers are expected to follow the board-level guidelines provided on the Microsemi SoC Products Group website. These guidelines are discussed in the datasheets and application notes (refer to the “Related Documents” section of the datasheet for application note links). Customers are also expected to troubleshoot board-level signal integrity issues by measuring voltages and taking oscilloscope plots.

Programming Failure Allowances

Microsemi has strict policies regarding programming failure allowances. Please refer to *Programming and Functional Failure Guidelines* on the Microsemi SoC Products Group website for details.

Contacting the Customer Support Group

Highly skilled engineers staff the Customer Applications Center from 7:00 A.M. to 6:00 P.M., Pacific time, Monday through Friday. You can contact the center by one of the following methods:

Electronic Mail

You can communicate your technical questions to our email address and receive answers back by email, fax, or phone. Also, if you have design problems, you can email your design files to receive assistance. Microsemi monitors the email account throughout the day. When sending your request to us, please be sure to include your full name, company name, and contact information for efficient processing of your request. The technical support email address is soc_tech@microsemi.com.

Telephone

Our Technical Support Hotline answers all calls. The center retrieves information, such as your name, company name, telephone number, and question. Once this is done, a case number is assigned. Then the center forwards the information to a queue where the first available applications engineer receives the data and returns your call. The phone hours are from 7:00 A.M. to 6:00 P.M., Pacific time, Monday through Friday.

The Customer Applications Center number is (800) 262-1060.

European customers can call +44 (0) 1256 305 600.

Table 12-6 and Table 12-7 show all available options. If you want to implement custom levels, refer to the "Advanced Options" section on page 322 for information on each option and how to set it.

3. When done, click **Finish** to generate the Security Header programming file.

Table 12-6 • All IGLOO and ProASIC3 Header File Security Options

Security Option	FlashROM Only	FPGA Core Only	Both FlashROM and FPGA
No AES / no FlashLock	✓	✓	✓
FlashLock only	✓	✓	✓
AES and FlashLock	✓	✓	✓

Note: ✓ = options that may be used

Table 12-7 • All Fusion Header File Security Options

Security Option	FlashROM Only	FPGA Core Only	FB Core Only	All
No AES / No FlashLock	✓	✓	✓	✓
FlashLock	✓	✓	✓	✓
AES and FlashLock	✓	✓	✓	✓

Generation of Programming Files with AES Encryption— Application 3

This section discusses how to generate design content programming files needed specifically at unsecured or remote locations to program devices with a Security Header (FlashLock Pass Key and AES key) already programmed ("Application 2: Nontrusted Environment—Unsecured Location" section on page 309 and "Application 3: Nontrusted Environment—Field Updates/Upgrades" section on page 310). In this case, the encrypted programming file must correspond to the AES key already programmed into the device. If AES encryption was previously selected to encrypt the FlashROM, FBs, and FPGA array, AES encryption must be set when generating the programming file for them. AES encryption can be applied to the FlashROM only, the FBs only, the FPGA array only, or all. The user must ensure both the FlashLock Pass Key and the AES key match those already programmed to the device(s), and all security settings must match what was previously programmed. Otherwise, the encryption and/or device unlocking will not be recognized when attempting to program the device with the programming file.

The generated programming file will be AES-encrypted.

In this scenario, generate the programming file as follows:

1. Deselect **Security settings** and select the portion of the device to be programmed (Figure 12-17 on page 320). Select **Programming previously secured device(s)**. Click **Next**.

Circuit Description

All IGLOO devices as well as the ProASIC3L product family are available in two versions: V5 devices, which are powered by a 1.5 V supply and V2 devices, which are powered by a supply anywhere in the range of 1.2 V to 1.5 V in 50 mV increments. Applications that use IGLOO or ProASIC3L devices powered by a 1.2 V core supply must have a mechanism that switches the core voltage from 1.2 V (or other voltage below 1.5 V) to 1.5 V during in-system programming (ISP). There are several possible techniques to meet this requirement. Microsemi recommends utilizing a linear voltage regulator, a resistor voltage divider, and an N-Channel Digital FET to set the appropriate VCC voltage, as shown in Figure 14-1.

Where 1.2 V is mentioned in the following text, the meaning applies to any voltage below the 1.5 V range. Resistor values in the figures have been calculated for 1.2 V, so refer to power regulator datasheets if a different core voltage is required.

The main component of Microsemi's recommended circuit is the LTC3025 linear voltage regulator from LinearTech. The output voltage of the LTC3025 on the OUT pin is set by the ratio of two external resistors, R37 and R38, in a voltage divider. The linear voltage regulator adjusts the voltage on the OUT pin to maintain the ADJ pin voltage at 0.4 V (referenced to ground). By using an R38 value of 40.2 k Ω and an R37 value of 80.6 k Ω , the output voltage on the OUT pin is 1.2 V. To achieve 1.5 V on the OUT pin, R44 can be used in parallel with R38. The OUT pin can now be used as a switchable source for the VCC supply. Refer to the *LTC3025 Linear Voltage Regulator datasheet* for more information.

In Figure 14-1, the N-Channel Digital FET is used to enable and disable R44. This FET is controlled by the JTAG TRST signal driven by the FlashPro3 programmer. During programming of the device, the TRST signal is driven HIGH by the FlashPro3, and turns the N-Channel Digital FET ON. When the FET is ON, R44 becomes enabled as a parallel resistance to R38, which forces the regulator to set OUT to 1.5 V.

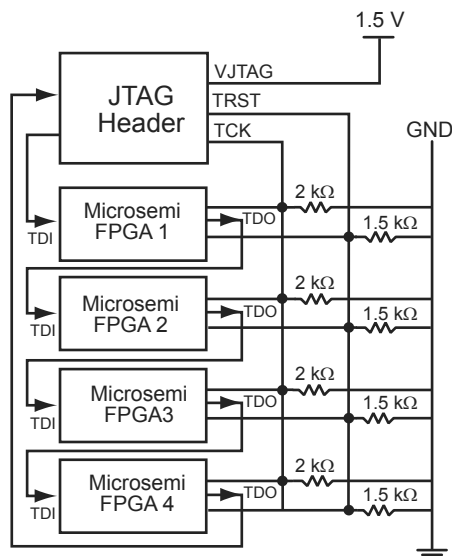
When the FlashPro3 is connected and not in programming mode or when it is not connected, the pull-down resistor, R10, will pull the TRST signal LOW. When this signal is LOW, the N-Channel Digital FET is "open" and R44 is not part of the resistance seen by the LTC3025. The new resistance momentarily changes the voltage value on the ADJ pin, which in turn causes the output of the LTC3025 to compensate by setting OUT to 1.2 V. Now the device will run in regular active mode at the regular 1.2 V core voltage.

Figure 14-1 • Circuit Diagram

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.1 (October 2008)	The "Introduction" was revised to include information about the core supply voltage range of operation in V2 devices.	341
	IGLOO nano device support was added to Table 14-1 • Flash-Based FPGAs Supporting Voltage Switching Circuit.	342
	The "Circuit Description" section was updated to include IGLOO PLUS core operation from 1.2 V to 1.5 V in 50 mV increments.	343
v1.0 (August 2008)	The "Microsemi's Flash Families Support Voltage Switching Circuit" section was revised to include new families and make the information more concise.	342



Note: TCK is correctly wired with an equivalent tie-off resistance of 500 Ω , which satisfies the table for VJTAG of 1.5 V. The resistor values for TRST are not appropriate in this case, as the tie-off resistance of 375 Ω is below the recommended minimum for VJTAG = 1.5 V, but would be appropriate for a VJTAG setting of 2.5 V or 3.3 V.

Figure 16-3 • Parallel Resistance on JTAG Chain of Devices

Advanced Boundary Scan Register Settings

You will not be able to control the order in which I/Os are released from boundary scan control. Testing has produced cases where, depending on I/O placement and FPGA routing, a 5 ns glitch has been seen on exiting programming mode. The following setting is recommended to prevent such I/O glitches:

1. In the FlashPro software, configure the advanced BSR settings for **Specify I/O Settings During Programming**.
2. Set the input BSR cell to **Low** for the input I/O.

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
August 2012	In the "Boundary Scan Chain" section, the reference made to the datasheet for pull-up/-down recommendations was changed to mention TCK and TRST pins rather than TDO and TCK pins. TDO is an output, so no pull resistor is needed (SAR 35937).	359
	The "Advanced Boundary Scan Register Settings" section is new (SAR 38432).	361
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Table 16-3 • TRST and TCK Pull-Down Recommendations was revised to add VJTAG at 1.2 V.	360
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 16-1 • Flash-Based FPGAs.	358
v1.3 (October 2008)	The "Boundary Scan Support in Low Power Devices" section was revised to include new families and make the information more concise.	359
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 16-1 • Flash-Based FPGAs: <ul style="list-style-type: none"> ProASIC3L was updated to include 1.5 V. The number of PLLs for ProASIC3E was changed from five to six. 	358
v1.1 (March 2008)	The chapter was updated to include the IGLOO PLUS family and information regarding 15 k gate devices.	N/A
	The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	358

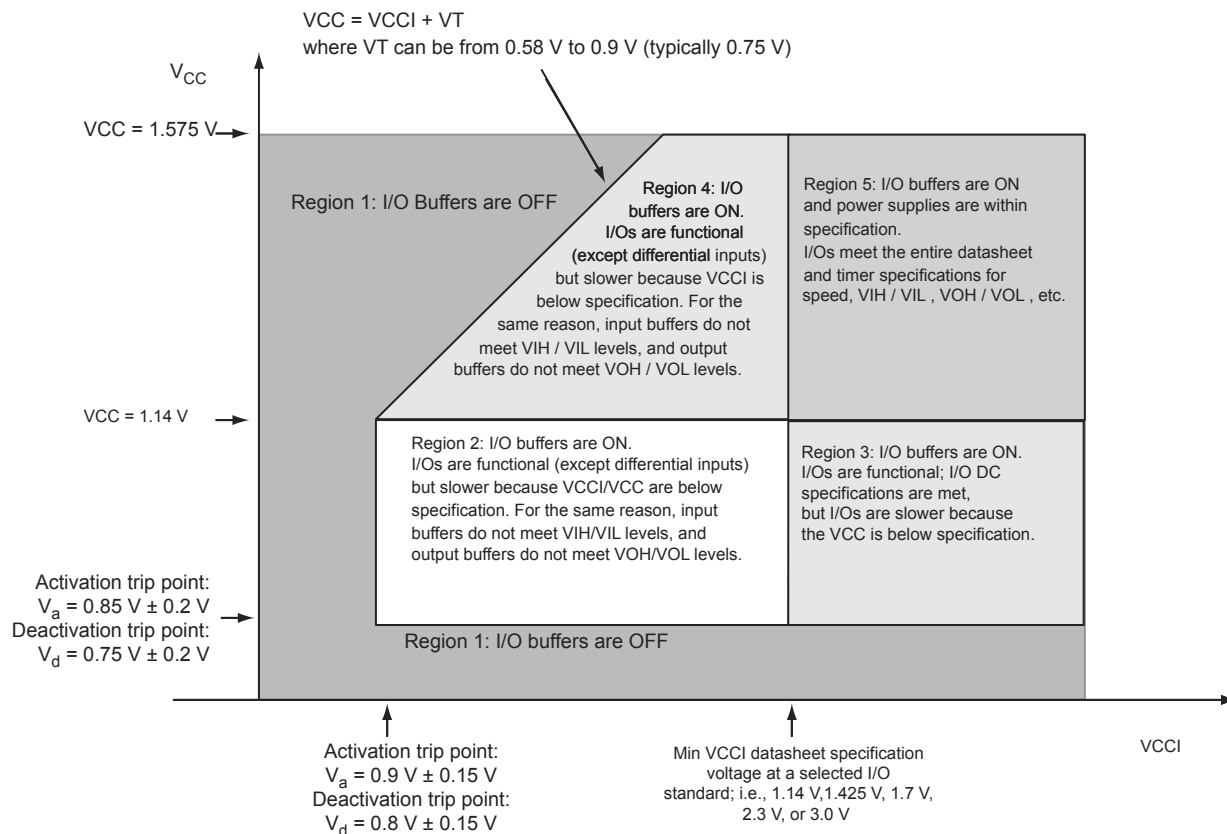


Figure 18-5 • I/O State as a Function of V_{CCI} and V_{CC} Voltage Levels for IGLOO V2, IGLOO nano V2, IGLOO PLUS V2, and ProASIC3L Devices Running at $V_{CC} = 1.2\text{ V} \pm 0.06\text{ V}$